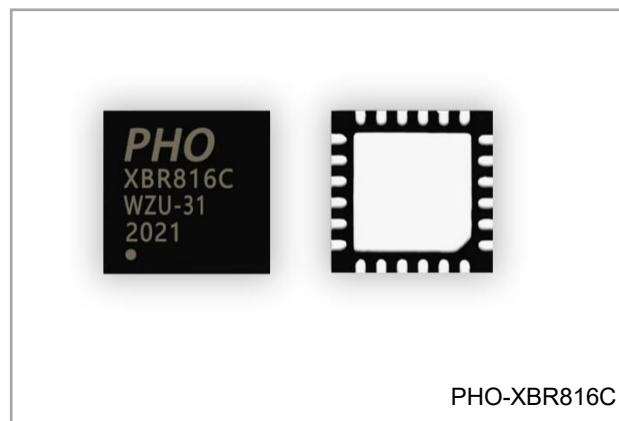


■ Introduction

The XBR816C is highly integrated X band Radar transceiver device in RF CMOS technology. The device is optimized for applications at higher temperatures and it is rated of operating up to 70°C.



Key Features

- ✧ 1.2V supply voltage
- ✧ Typical 60mA current for default mode
- ✧ Fully integrated 10.525 GHz CMOS transceiver
- ✧ Single-ended transmitter and receiver
- ✧ Max 1dBm transmit output power
- ✧ < -95dBm receiver sensitivity
- ✧ Harmonic rejection: > 40dBc
- ✧ Output noise voltage: max 0.5uVrms for low gain and max 45uVrms for high gain
- ✧ Operation condition: -40°C ~ 70°C
- ✧ QFN 24 pins, 4mm x 4mm package

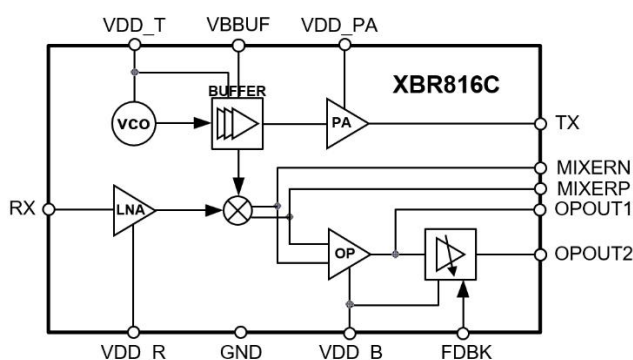
Key Benefits

- ✧ Low power consumption
- ✧ Small system size
- ✧ Low system cost

Applications

- ✧ Smart Radar Sensor
- ✧ Lighting Controller
- ✧ Security & Surveillance Products
- ✧ Industrial Applications
- ✧ Consumer Appliances

System Diagram

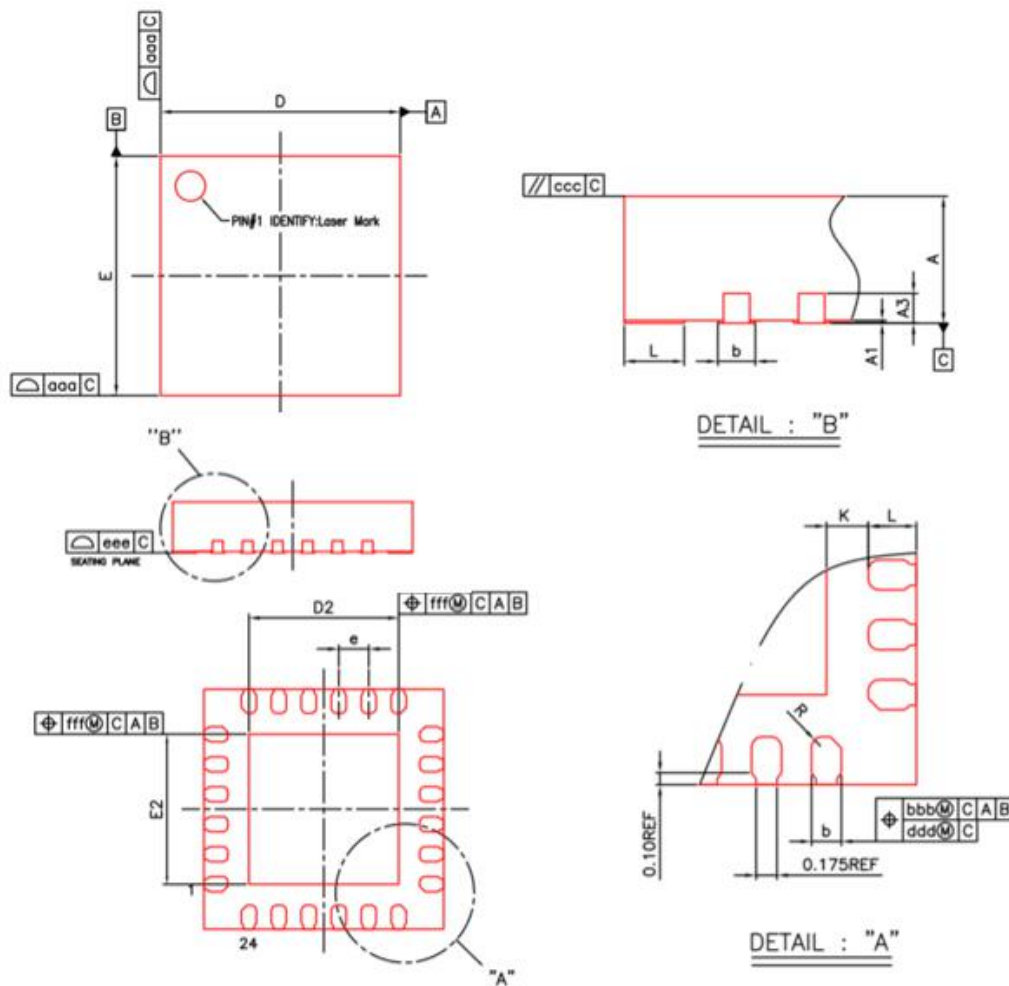


■ Pin assignment

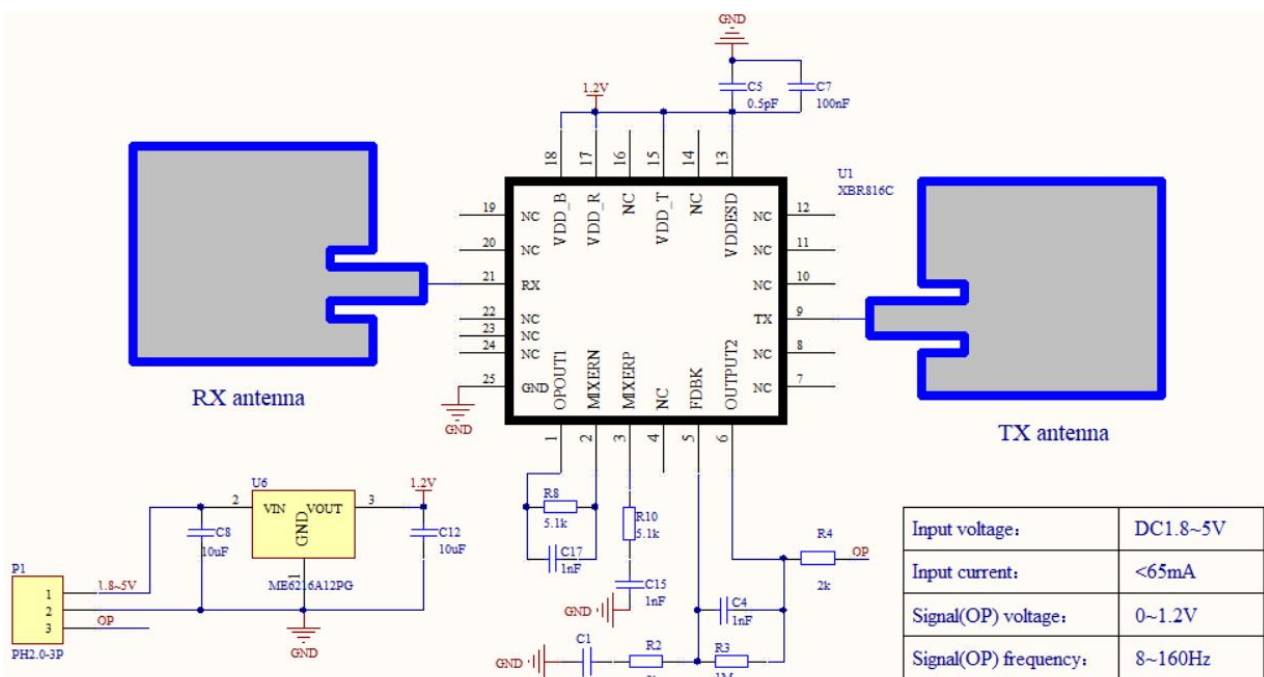
PIN Number	PIN Name	Function
1	OPOUT1	First stage OP IF output
2	MIXERN	Raw IF Signal output N
3	MIXERP	Raw IF Signal output P
5	FDBK	OP Feedback Loop
6	OPOUT2	Second stage OP IF output
9	TXN	RF Signal OUT
13	VDDPA	1.2V supply for power amplifier
15	VDD_T	1.2V supply for transmitter
17	VDD_R	1.2V supply for receiver
18	VDD_B	1.2V supply for baseband
21	RX	RF Signal IN
4,7,8,10,11,12,14,16 19,20,22,23,24	NC	Not connected
25	VSS	Ground

■ Package information

Symbol	Dimension in mm			Dimension in inch		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.85	0.90	0.031	0.033	0.035
A1	0.00	0.02	0.05	0.000	0.001	0.002
A3	0.20 REF			0.008 REF		
b	0.18	0.25	0.30	0.007	0.010	0.012
D/E	4.00 BSC			0.157 BSC		
D2/E2	2.35	2.50	2.65	0.093	0.098	0.104
e	0.50 BSC			0.020 BSC		
L	0.30	0.40	0.50	0.012	0.016	0.020
K	0.20	---	---	0.008	---	---
R	0.09	---	---	0.004	---	---
aaa	---	---	0.15	---	---	0.006
bbb	---	---	0.10	---	---	0.004
ccc	---	---	0.10	---	---	0.004
ddd	---	---	0.05	---	---	0.002
eee	---	---	0.08	---	---	0.003
fff	---	---	0.10	---	---	0.004



Reference Design



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